

# MOSFET

## OptiMOS™ 3 Power-Transistor, 200 V

### Features

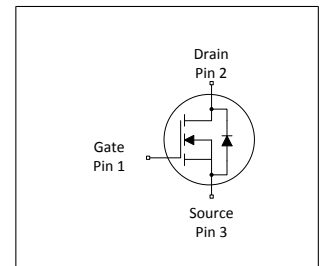
- Ideal for high frequency switching and sync. rec.
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

### Product validation

Qualified according to JEDEC Standard

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	200	V
$R_{DS(on),max}$	32	m $\Omega$
$I_D$	26	A
$Q_{oss}$	54	nC
$Q_G(0V..10V)$	22	nC



Type / Ordering Code	Package	Marking	Related Links
IPA320N20NM3S	PG-TO 220 FullPAK	320N203S	-

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	26 19	A	$V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	104	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	-	-	190	mJ	$I_D=26\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	38	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j$ , $T_{stg}$	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	3.9	°C/W	-

## 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	200	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}$ , $I_D=89\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=160\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=160\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	27.2	32.0	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=26\text{ A}$
Gate resistance <sup>3)</sup>	$R_G$	-	2.5	-	$\Omega$	-
Transconductance	$g_{fs}$	-	48	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$ , $I_D=26\text{ A}$

<sup>1)</sup> See Diagram 3 for more detailed information

<sup>2)</sup> See Diagram 13 for more detailed information

<sup>3)</sup> Defined by design. Not subject to production test.

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance <sup>1)</sup>	$C_{iss}$	-	1800	2300	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	140	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	-	5	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	11	-	ns	$V_{DD}=100\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=13\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Rise time	$t_r$	-	9	-	ns	$V_{DD}=100\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=13\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	21	-	ns	$V_{DD}=100\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=13\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Fall time	$t_f$	-	4	-	ns	$V_{DD}=100\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=13\text{ A}$ , $R_{G,ext}=1.6\ \Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	8	-	nC	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	5	-	nC	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	3	-	nC	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	5	-	nC	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	22	30	nC	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.3	-	V	$V_{DD}=100\text{ V}$ , $I_D=13\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	20	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	54	-	nC	$V_{DD}=100\text{ V}$ , $V_{GS}=0\text{ V}$

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	26	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	104	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.94	1.2	V	$V_{GS}=0\text{ V}$ , $I_F=26\text{ A}$ , $T_J=25\text{ °C}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	500	-	nC	$V_R=100\text{ V}$ , $I_F=13\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

## 4 Electrical characteristics diagrams

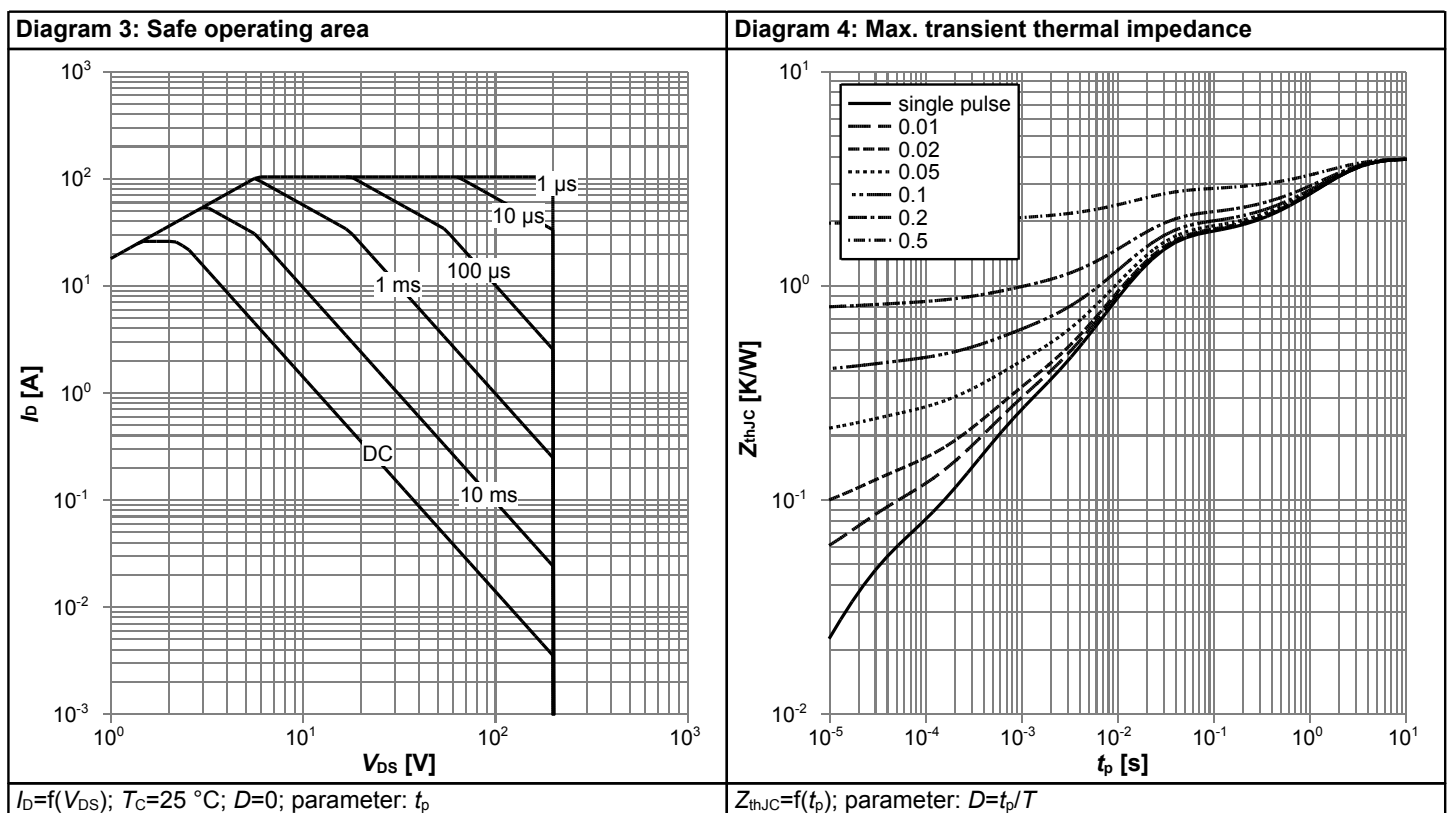
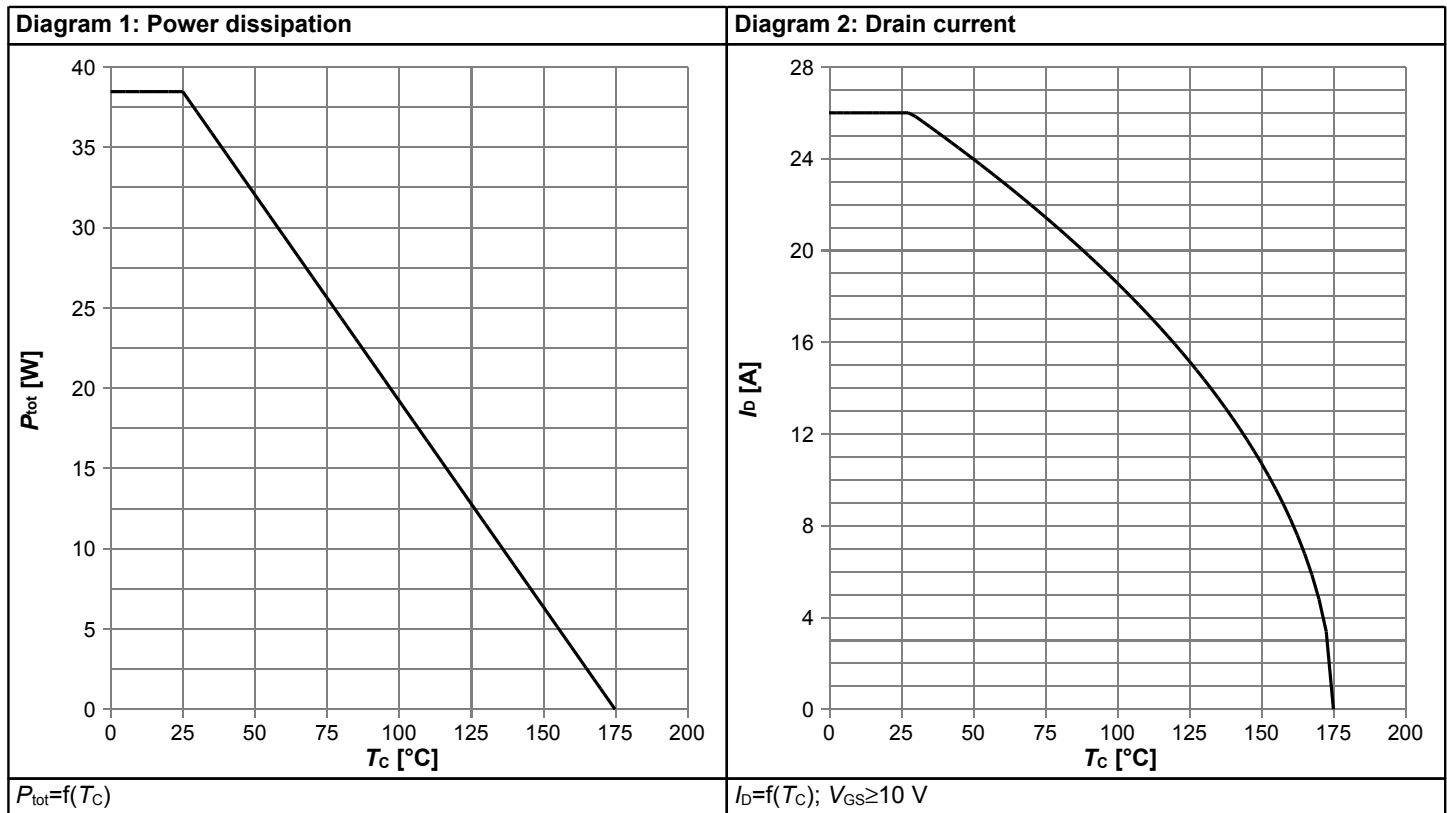
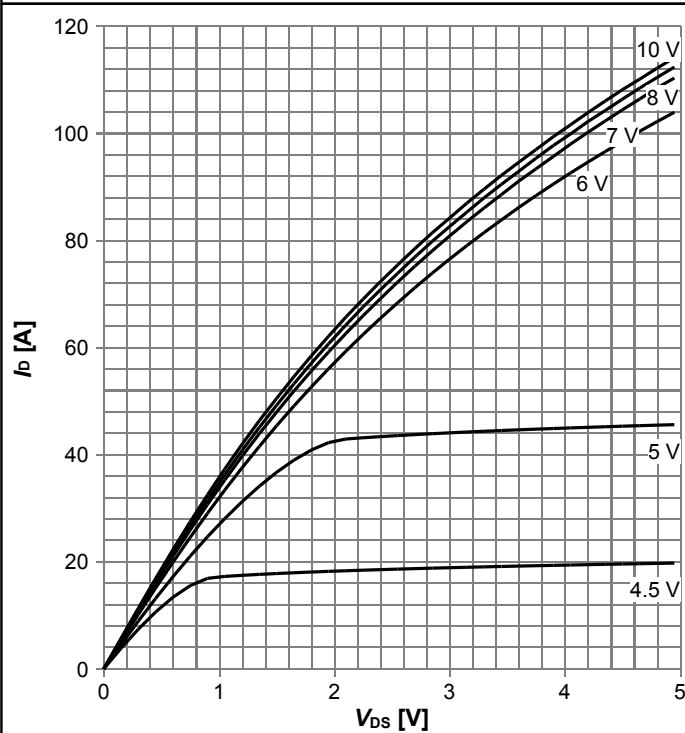
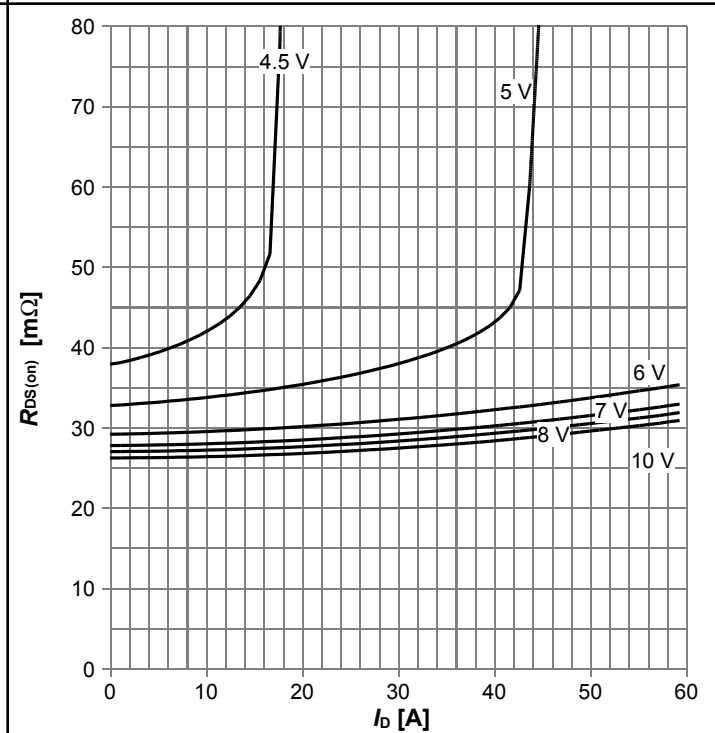


Diagram 5: Typ. output characteristics



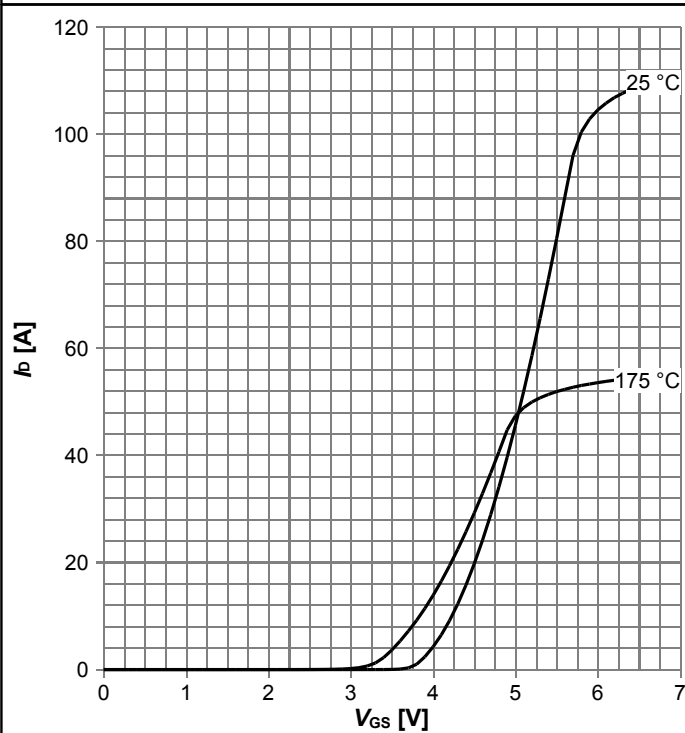
$I_D = f(V_{DS})$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



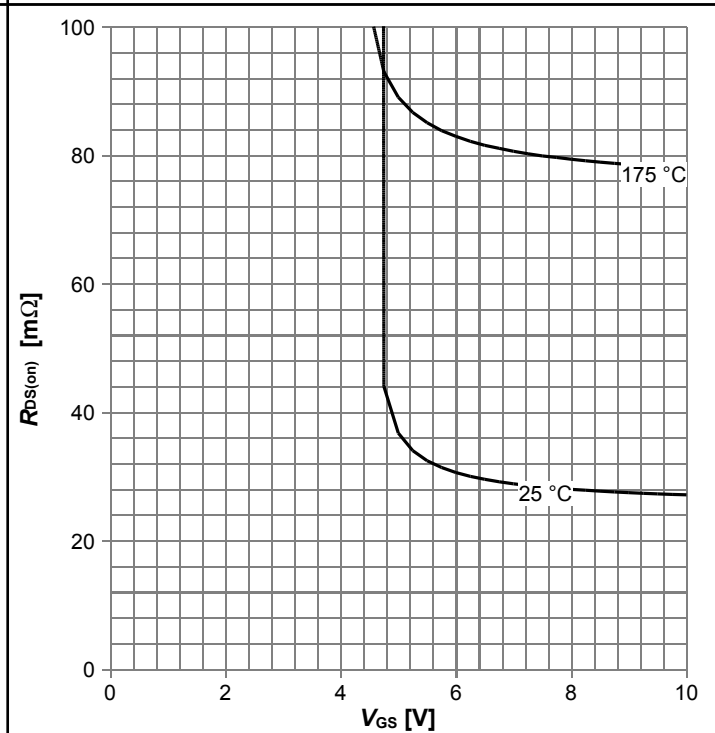
$R_{DS(on)} = f(I_D)$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



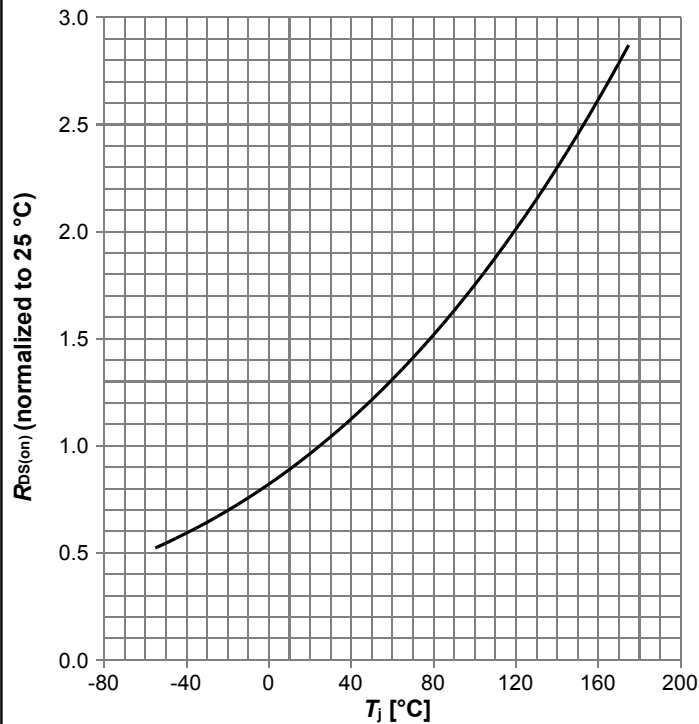
$I_D = f(V_{GS})$ ,  $|V_{DS}| > 2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. drain-source on resistance



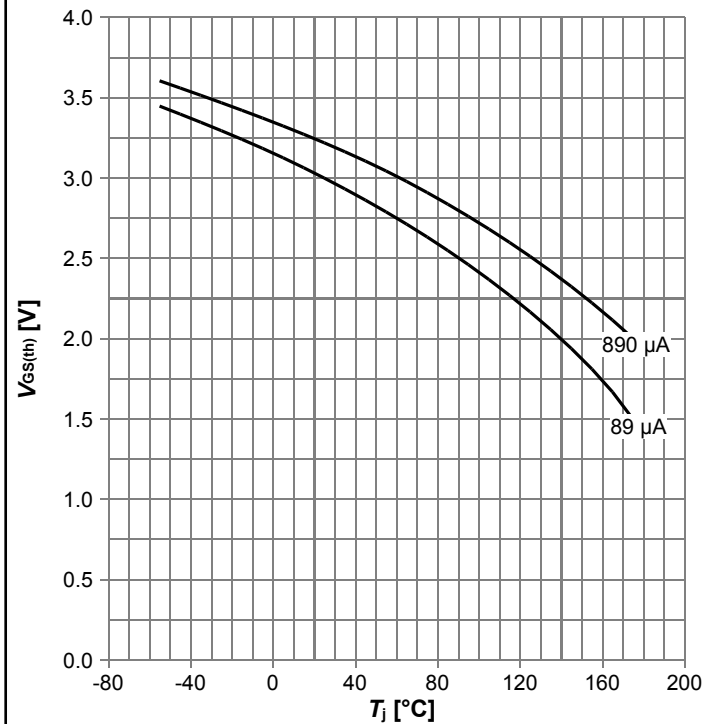
$R_{DS(on)} = f(V_{GS})$ ,  $I_D = 26\text{ A}$ ; parameter:  $T_j$

Diagram 9: Normalized drain-source on resistance



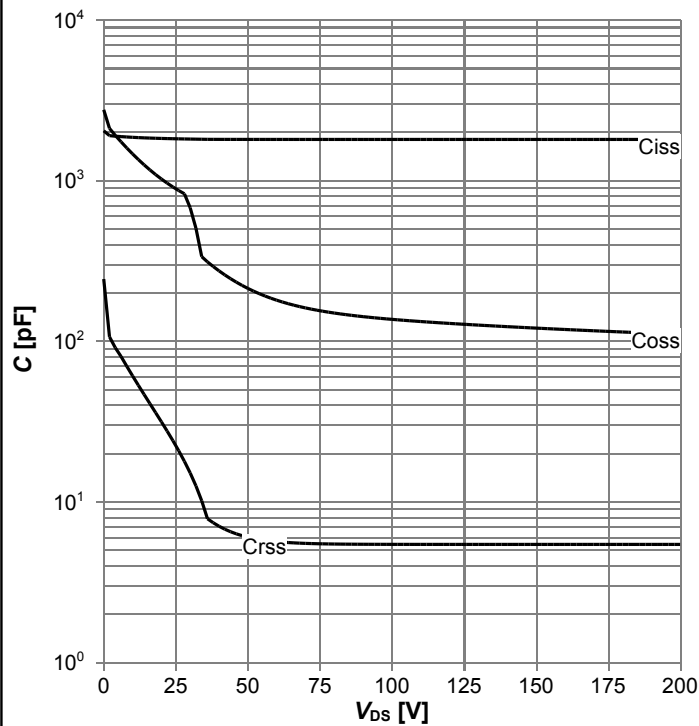
$R_{DS(on)} = f(T_j)$ ,  $I_D = 26 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$

Diagram 10: Typ. gate threshold voltage



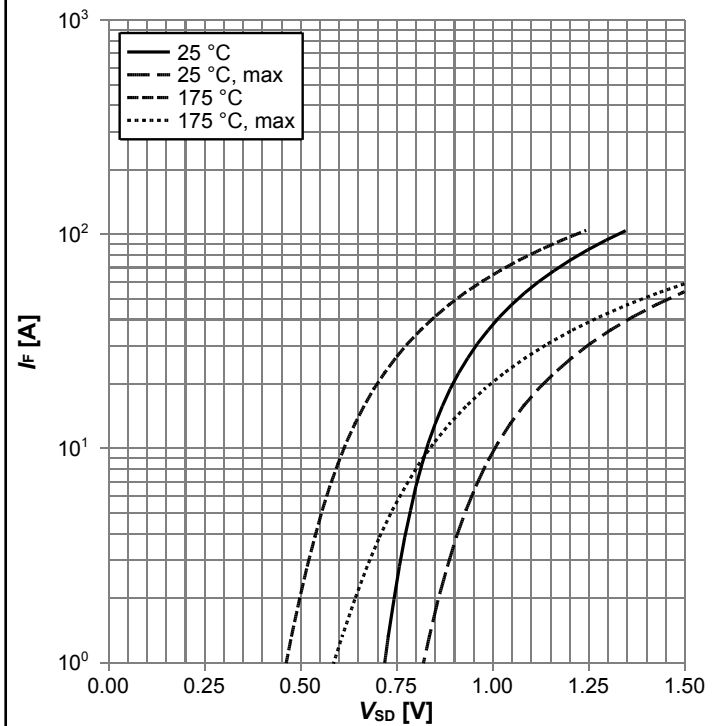
$V_{GS(th)} = f(T_j)$ ,  $V_{GS} = V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



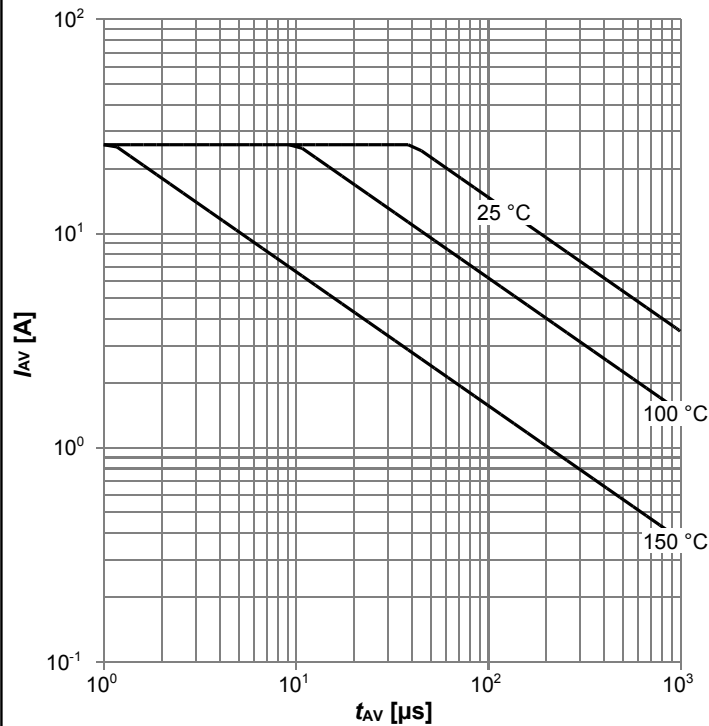
$C = f(V_{DS})$ ;  $V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



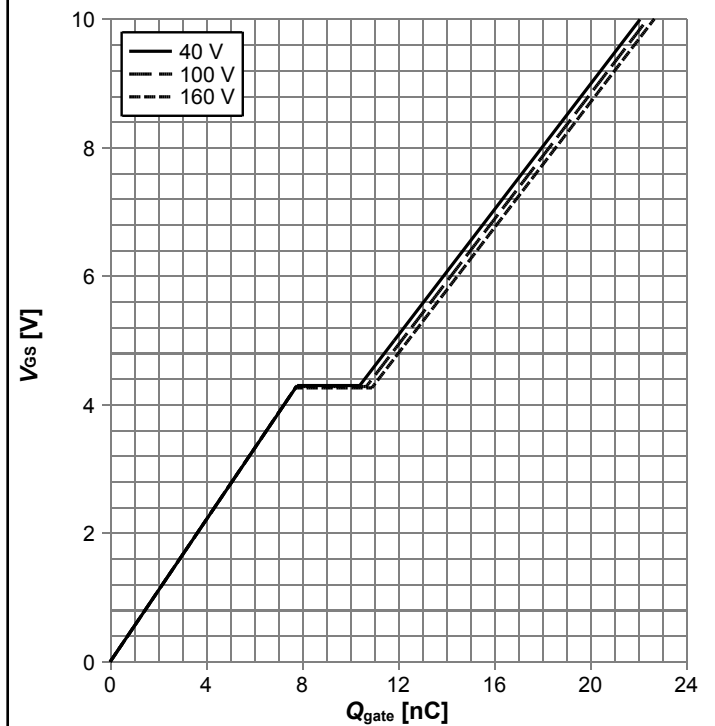
$I_F = f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics



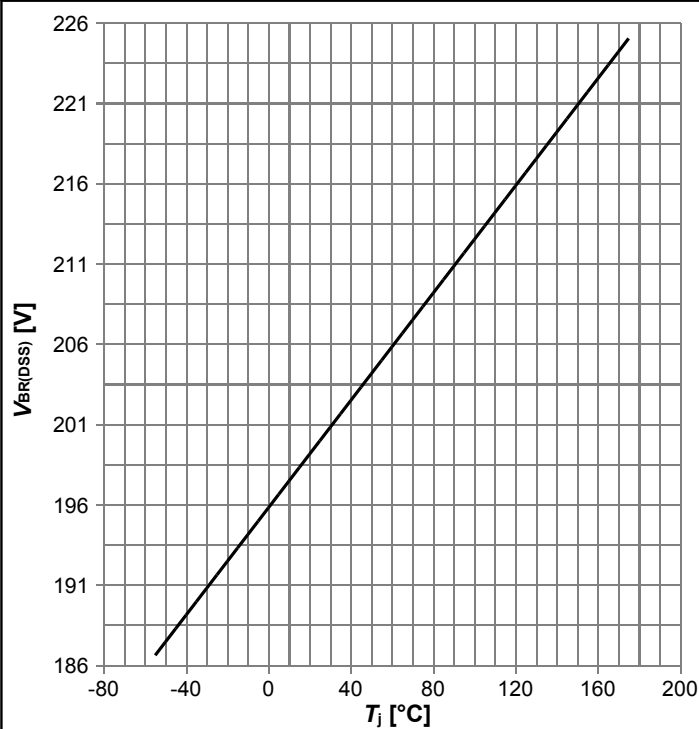
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25\ \Omega$ ; parameter:  $T_{j,start}$

Diagram 14: Typ. gate charge



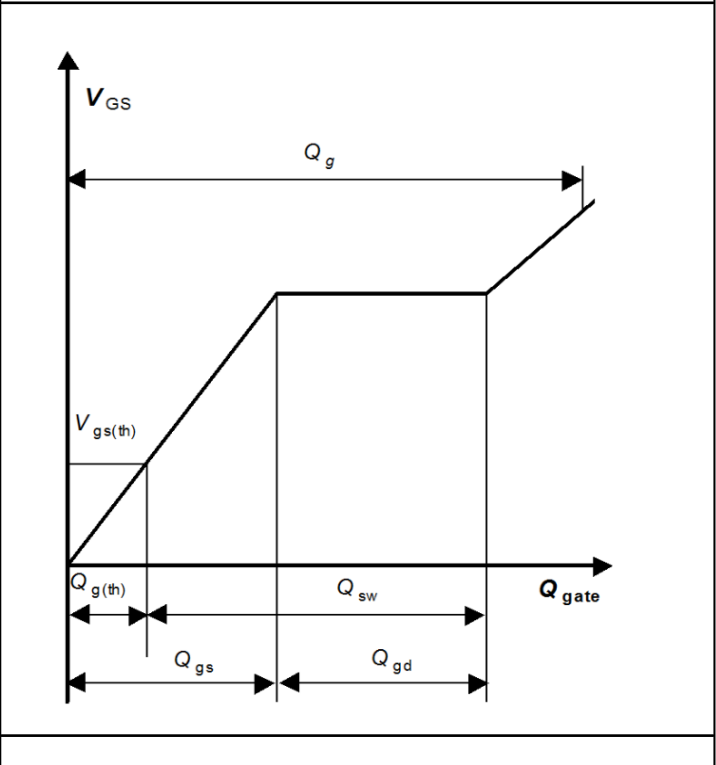
$V_{GS}=f(Q_{gate})$ ,  $I_D=13\text{ A}$  pulsed,  $T_j=25\text{ °C}$ ; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



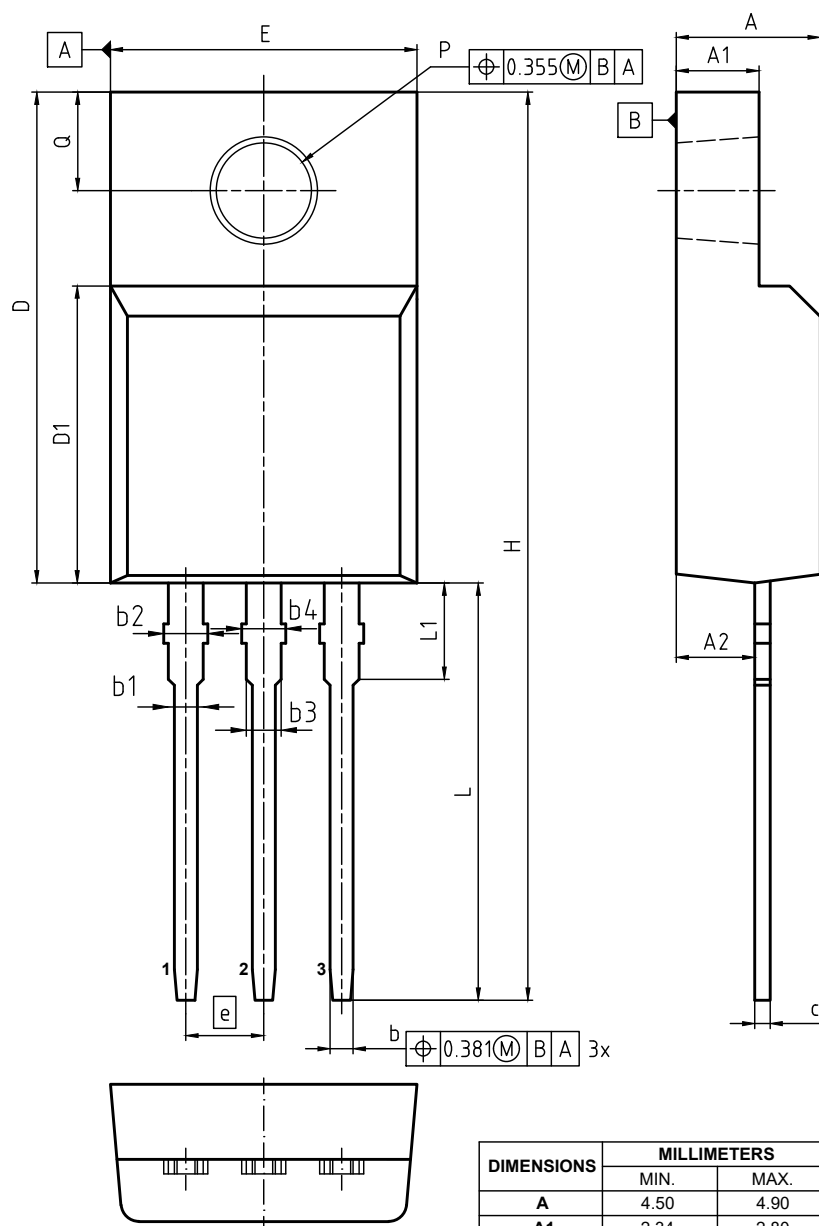
$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1\text{ mA}$

Diagram Gate charge waveforms





## 5 Package Outlines



NOTES:  
STANDARD QUALITY GRADE  
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PRO-  
TRUSIONS OR GATE BURRS

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.50	4.90
A1	2.34	2.80
A2	2.42	2.86
b	0.65	0.90
b1	0.95	1.38
b2	1.20	1.50
b3	0.65	1.38
b4	1.20	1.50
c	0.40	0.63
D	15.67	16.15
D1	8.97	9.83
E	10.00	10.65
e	2.54	
H	28.70	29.75
L	12.78	13.75
L1	2.83	3.45
øP	3.00	3.38
Q	3.15	3.50

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Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm/inches

## Revision History

IPA320N20NM3S

**Revision: 2019-09-02, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-07-18	Release of final version
2.1	2019-09-02	Update package outline

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